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Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references at the end of each chapters and index.
Nota di contenuto	CONTENTS; PREFACE ; LIST OF CONTRIBUTORS ; Introduction to Organic Light-Emitting Display Technologies ; INTRODUCTION; DEVELOPEMNT HISTORY OF OLEDs; BASIC PHYSICS OF OLEDs; Charge Carriers Injection; Charge Carriers Transportation ; Exciton Formation and Recombination ; Light Extraction from Devices ; FABRICATION AND CHARACTERIZATION OF OLEDs; APPLICATION OF OLEDs; Flat Panel Display; Solid-state Lighting; CONFLICT OF INTEREST; ACKNOWLEDGMENTS; REFERENCES; White Organic Light-Emitting Diodes for Display and Lighting Application ; WOLEDs FOR FULL COLOR DISPLAYS; WOLEDs FOR SOLID-STATE LIGHTING APPROACHES TO WHITE LIGHT EMISSIONMulti-emissive Layers; Single-emissive Layer; WOLEDs with Fluorescent-phosphorescent Hybrid Emitters ; Tandem WOLEDs; Side by Side WOLEDs; Color Converted WOLEDs; Excimer/Exciplex WOLEDs; CONFLICT OF INTEREST; ACKNOWLEDGMENTS; REFERENCES; Light Outcoupling Technologies ; INTRODUCTION; LIGHT DISTRIBUTION IN OLED; EXTERNAL EXTRACTION STRUCTURES; Truncated Square-pyramid Luminaire; Scattering Film; Sand-blasting Substrate; Microlens Array; INTERNAL EXTRACTION STRUCTURES; Internal Scattering Layer; Photonic Crystal Structure; Metal Nanoparticles; CONCLUSION

CONFLICT OF INTERESTACKNOWLEDGEMENTS; REFERENCES;  
Encapsulation Technologies ; INTRODUCTION; DARK SPOTS  
FORMATION MECHANISM; REQUIREMENT AND MEASUREMENT OF THE  
PERMEATION RATES; TRADITIONAL ENCAPSULATION TECHNOLOGY;  
THIN FILM ENCAPSUTION TECHNOLOGY; Si<sub>3</sub>N<sub>4</sub>/SiO<sub>2</sub> Multilayer;  
Organic/Inorganic Multilayer; Atomic Layer Deposited (ALD) Film;  
CONCLUSION; CONFLICT OF INTEREST; ACKNOWLEDGEMENTS;  
REFERENCES; Thin Film Transistor Technology ; INTRODUCTION;  
HISTORY OF THIN FILM TRANSISTORS; HYDROGENATED AMORPHOUS  
SILICON TFT TECHNOLOGY; LOW TEMPERATURE POLYCRYSTALLINE  
SILICON TFT TECHNOLOGY  
SPC TechnologyMIC Technology; ELA Technology; Bridge Grain  
Technology; METAL OXIDE SEMICONDUCTOR TFTS; Zinc Oxide TFTs;  
Amorphous Oxide Semiconductors and TFTs; Zinc Tin Oxide; Indium  
Gallium Oxide; Indium Gallium Zinc Oxide; GaN TFTs; MoS<sub>2</sub> TFTs;  
SUMMARY ; CONFLICT OF INTEREST; ACKNOWLEDGEMENTS;  
REFERENCES; Driving Schemes and Design Considerations for AMOLED ;  
CIRCUIT FUNDAMENTALS ; Resistor-Capacitor Circuit; Charging and  
Discharging RC Circuit; Capacitive Parasitics; TFT CIRCUIT  
CONSIDERATIONS; Operational Region; Transistor as a Switch;  
Transistor as a Current Source or Current Drain  
On ResistanceApproximation of TFT with an equivalent resistance;  
DESIGN CONSIDERATIONS FOR ACTIVE-MATRIX BACKPLANE; Brightness;  
Display Timing; Pixel Storage Capacitance; Design Expression; TFT  
CIRCUIT DESIGN TECHNIQUES; Bootstrap Circuit; CIRCUIT  
COMPENSATION AND LAYOUT DESIGN; CHALLENGE IN AMOLED  
DISPLAYS; Aging of OLED and TFT ; Threshold Voltage Shift; 2T1C Pixel  
Configuration; THRESHOLD VOLTAGE COMPENSATED AMOLED PIXEL;  
3T1C Pixel Configuration; 4T1C Pixel Configuration; 5T2C Pixel  
Configuration; 6T1C Pixel Configuration; 6T1C Pixel Configuration with  
biased discharge method  
CONFLICT OF INTEREST

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